

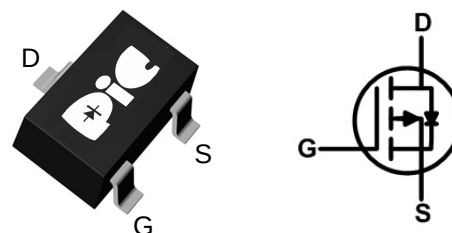
➤ General Description

This PAP3033ANS P-Channel enhancement mode power field effect transistor is the high density trench technology and this advanced technology can provide excellent $R_{DS(ON)}$ performance and efficiency for power switching and load switching application., this device also comply with the RoHS and Green Product requirement with full function reliability approved.

➤ Feature

- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- SOT-23S package design

➤ SOT-23S



➤ Application

- Battery Switch for Portable Devices
- Computers
 - Bus Switch
 - Load Switch LED Display

➤ Absolute Maximum Ratings

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	-30	V
Gate –Source Voltage		V_{GSS}	± 20	V
Continuous Drain Current($T_J=150^\circ C$)	$T_A=25^\circ C$	I_D	-4.0	A
	$T_A=70^\circ C$		-2.8	
Pulsed Drain Current		I_{DM}	-15	A
Continuous Source Current(Diode Conduction)		I_S	-1.5	A
Power Dissipation	$T_A=25^\circ C$	P_D	1.25	W
	$T_A=70^\circ C$		0.8	
Operating Junction Temperature		T_J	150	$^\circ C$
Storage Temperature Range		T_{STG}	-55/150	$^\circ C$
Thermal Resistance-Junction to Ambient		$R_{\theta JA}$	120	$^\circ C / W$

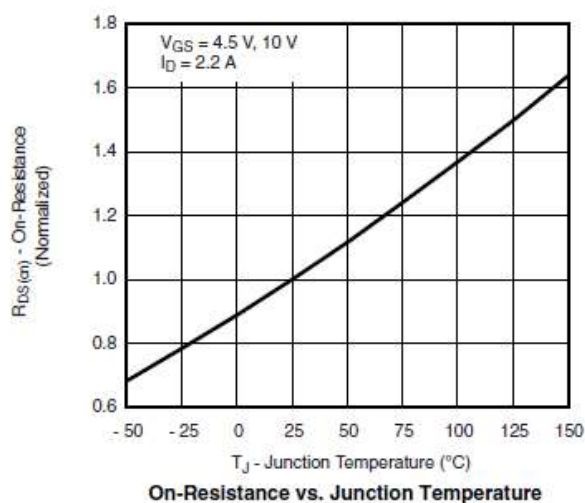
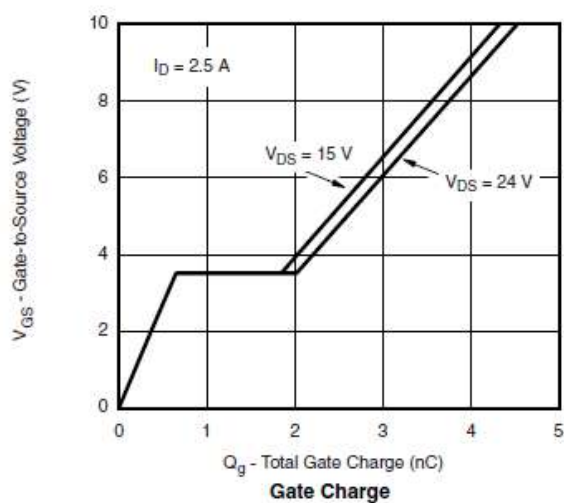
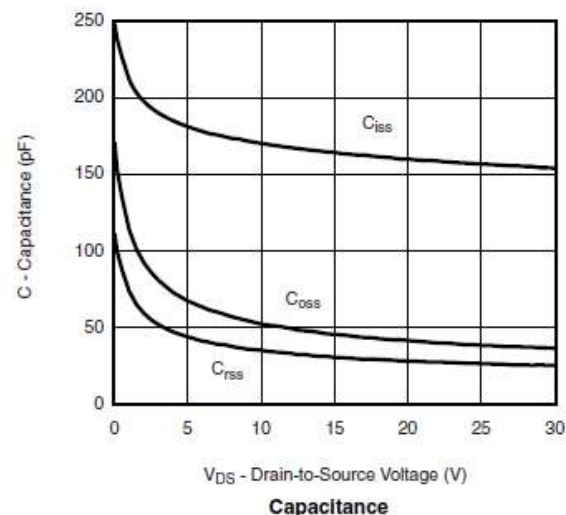
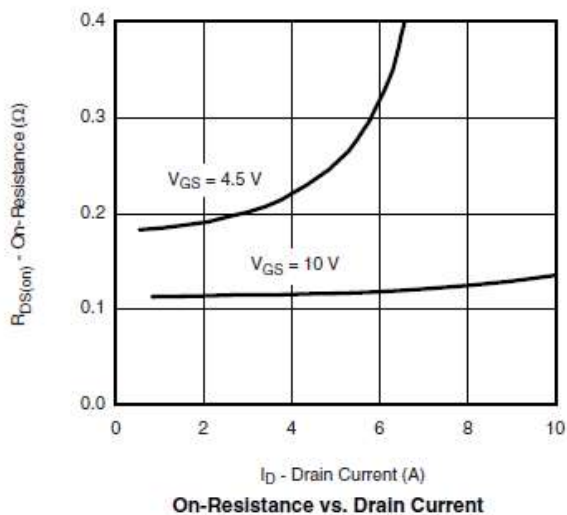
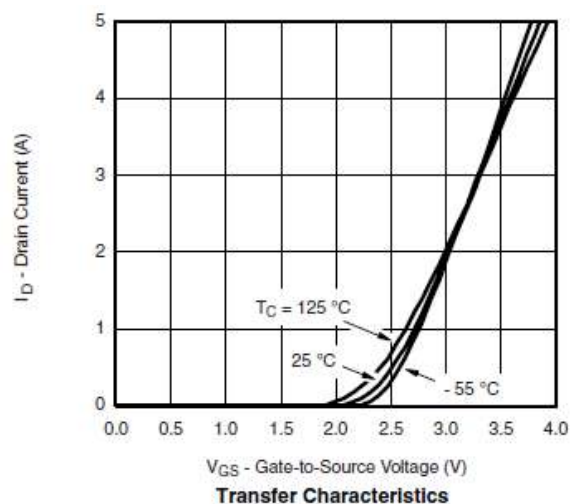
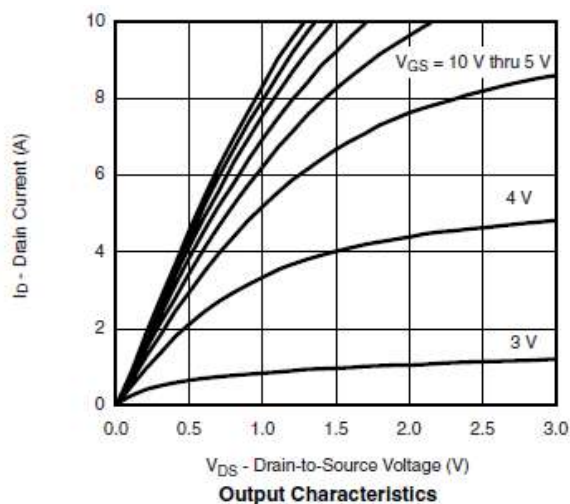
P-Ch -30V Fast Switching MOSFET
 $V_{DS}=-30V$, $I_D=-4.0A$, $R_{DS(on)}=90m\Omega$

➤ **Electrical Characteristics ($T_A=25^\circ C$ Unless otherwise noted)**

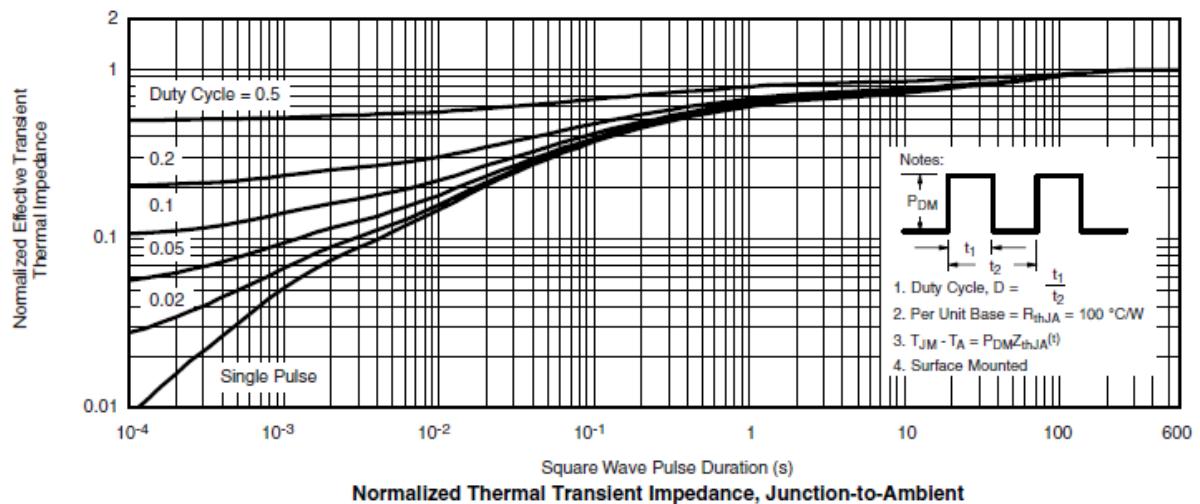
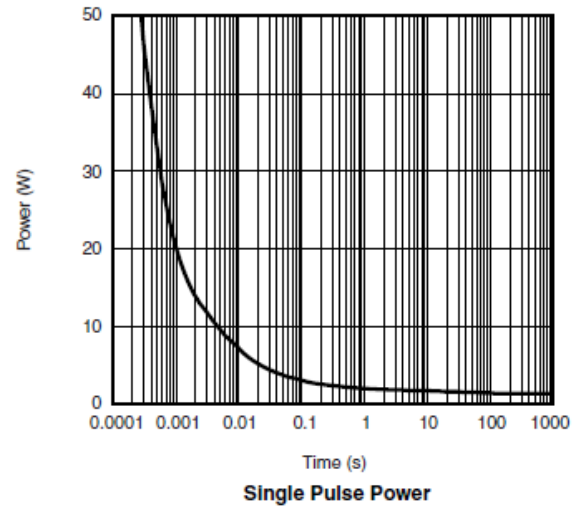
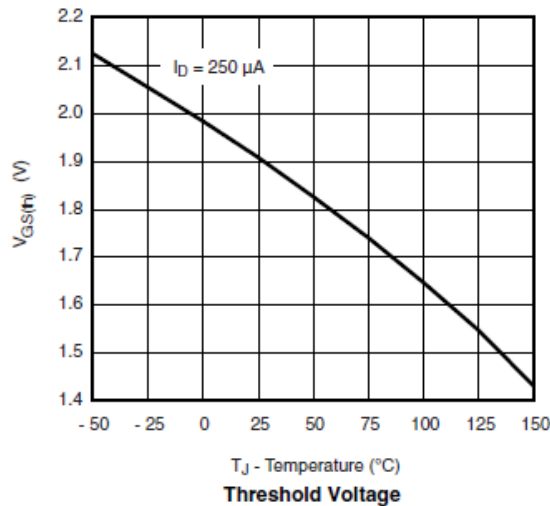
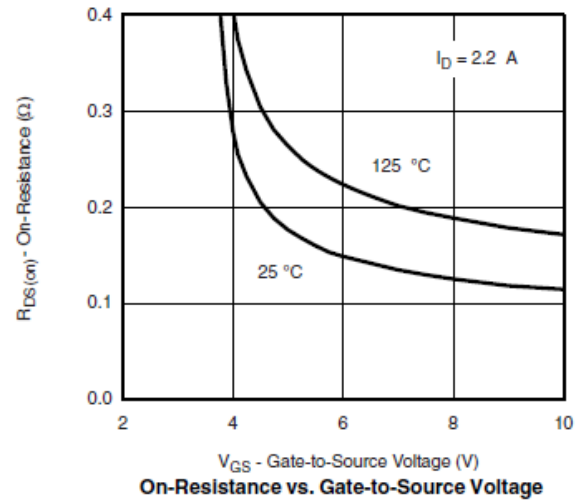
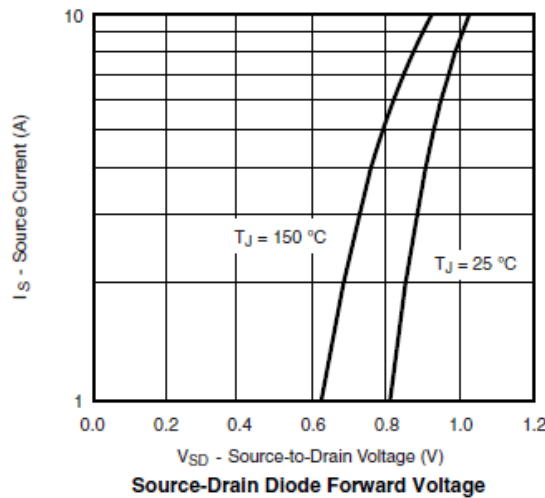
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-30			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.0		-2.5	
Gate Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-24V, V_{GS}=0V$			-1	uA
		$V_{DS}=-24V, V_{GS}=0V$ $T_A=85^\circ C$			-30	
On-State Drain Current	$I_{D(on)}$	$V_{DS} \leq -5V, V_{GS}=-10V$	-10			A
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=-10.0V, I_D=-4.0A$		76	90	mΩ
		$V_{GS}=-4.5V, I_D=-2.8A$		106	125	
Forward Transconductance	g_{FS}	$V_{DS}=-5V, I_D=-4.0A$		10		S
Diode Forward Voltage	V_{SD}	$I_S=-1.5A, V_{GS}=0V$		-0.7	-1.3	V
Dynamic						
Total Gate Charge	Q_g	$V_{DS}=-15V, V_{GS}=-4.5V$ $I_D=-2.5A$		2.5		nC
Gate-Source Charge	Q_{gs}			0.8		
Gate-Drain Charge	Q_{gd}			1.0		
Input Capacitance	C_{iss}	$V_{DS}=-15V, V_{GS}=0V$ $f=1MHz$		170		pF
Output Capacitance	C_{oss}			50		
Reverse Transfer Capacitance	C_{rss}			30		
Turn-On Time	$t_{d(on)}$	$V_{DD}=-15V, R_L=7.5\Omega$ $I_D=-2.0A, V_{GEN}=-10V$ $R_G=1\Omega$		5	10	ns
	t_r			10	16	
Turn-Off Time	$t_{d(off)}$			10	16	
	t_f			5	10	

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➤ Typical Characteristics

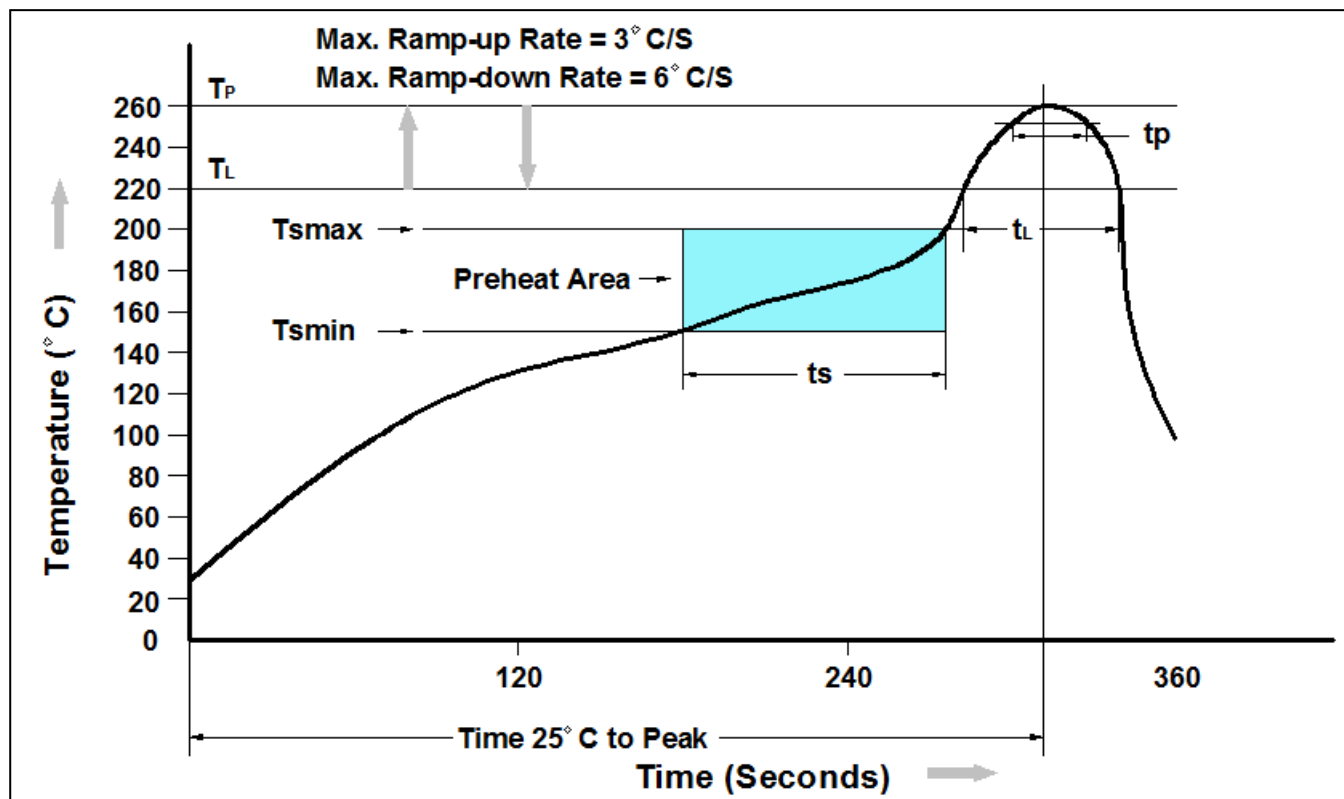


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➤ Recommand IR Reflow Soldering Thermal Profile



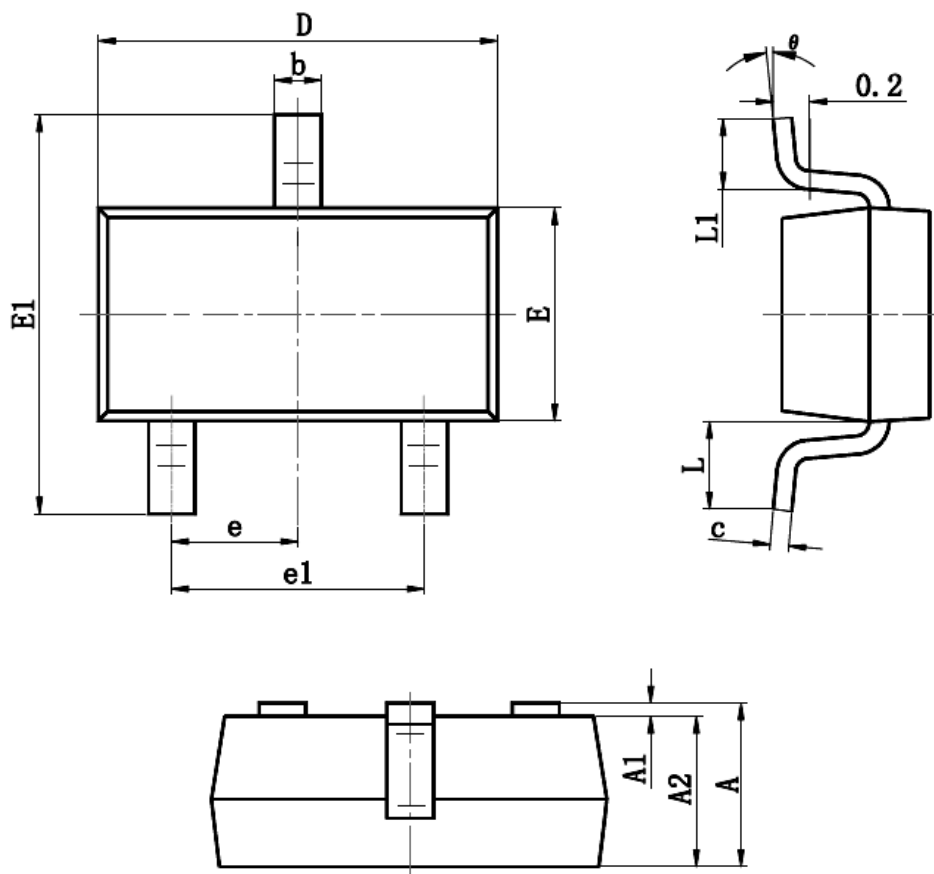
Profile Feature	Pb-Free Assembly Profile
Temperature Min. (T_{smin})	150°C
Temperature Max. (T_{smax})	200°C
Time (t_s) from (T_{smin} to T_{smax})	60-120 seconds
Average Ramp-up Rate (t_L to t_P)	3°C/second max.
Liquidous Temperature (T_L)	217°C
Time (t_L) Maintained Above (T_L)	60 – 150 seconds
Peak Temperature	260°C +0°C / -5°C
Time (t_P) within 5°C of actual Peak Temperature	30 seconds
Ramp-down Rate (T_P to T_L)	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.

➤ Ordering Information

Part Number	Description	Quantity
PAP3033ANS	SOT-23S Reel	3000 pcs

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➤ Package Information (SOT-23S)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.200	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.100	0.035	0.039
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	6°

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